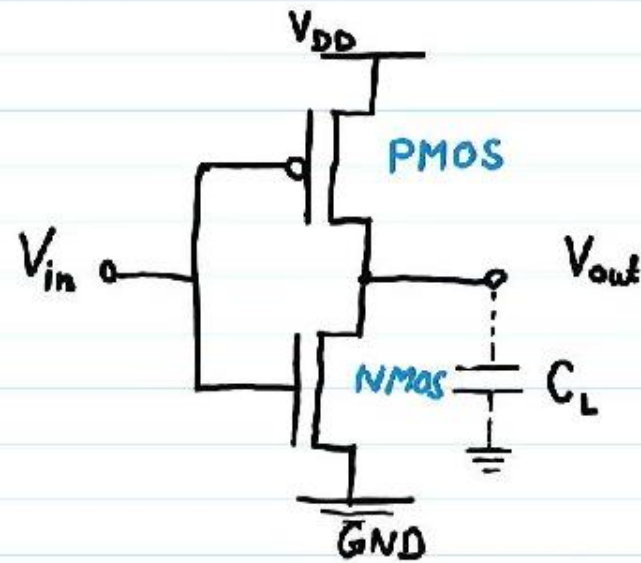


The CMOS Inverter :

- PMOS as well as NMOS.

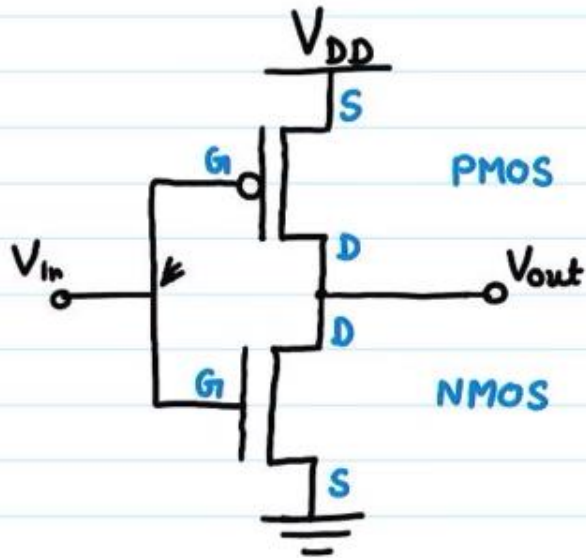


- Nucleus of ICs

- Same analysis can be extended to study complex gates (NAND, NOR etc.)

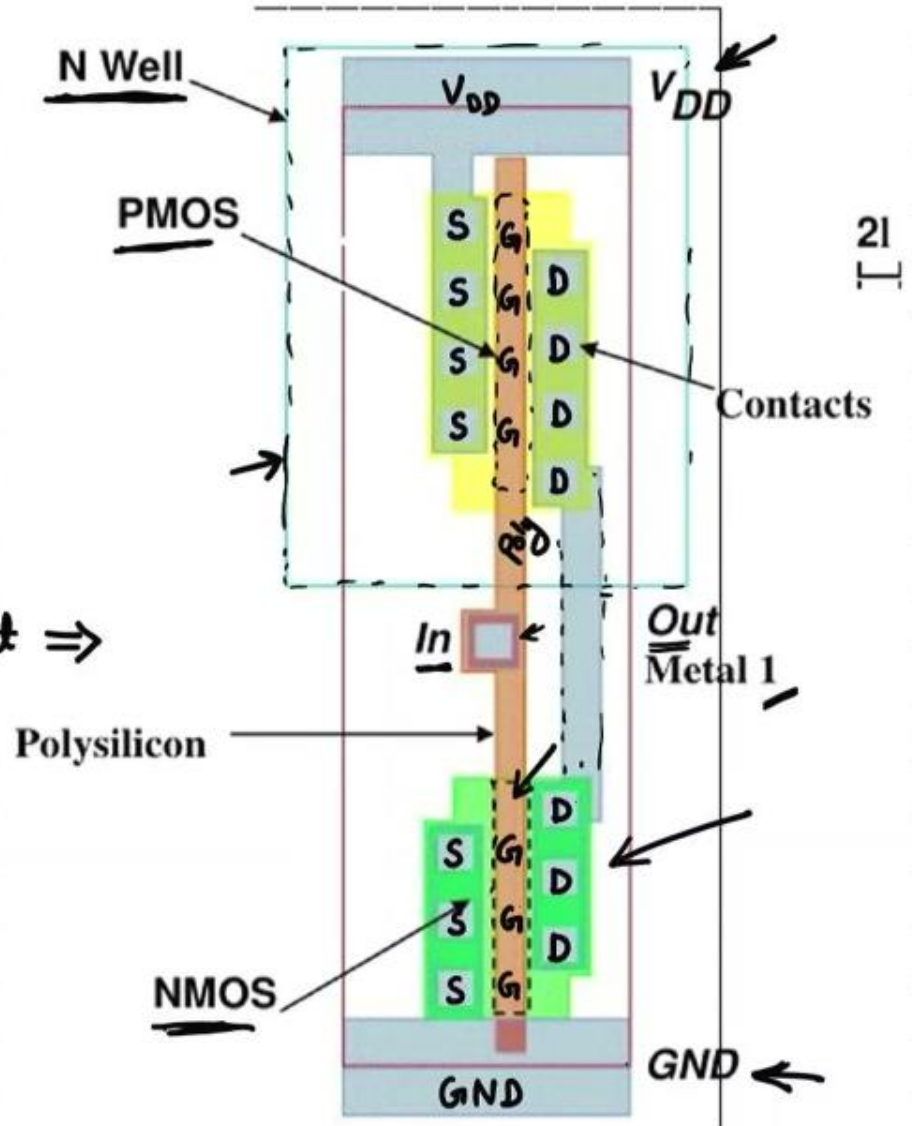
- 1 - Cost (Area and Complexity)
- 2 - Robustness (Static behavior)
- 3 - Performance (Dynamic / Transient response)
- 4 - Energy Efficiency (Power consumption)

CMOS Inverter (Schematic vs Layout) :

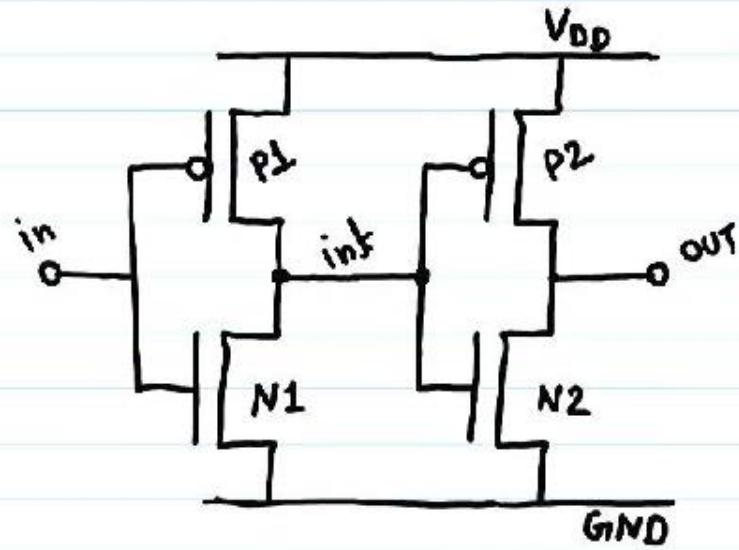


Schematic

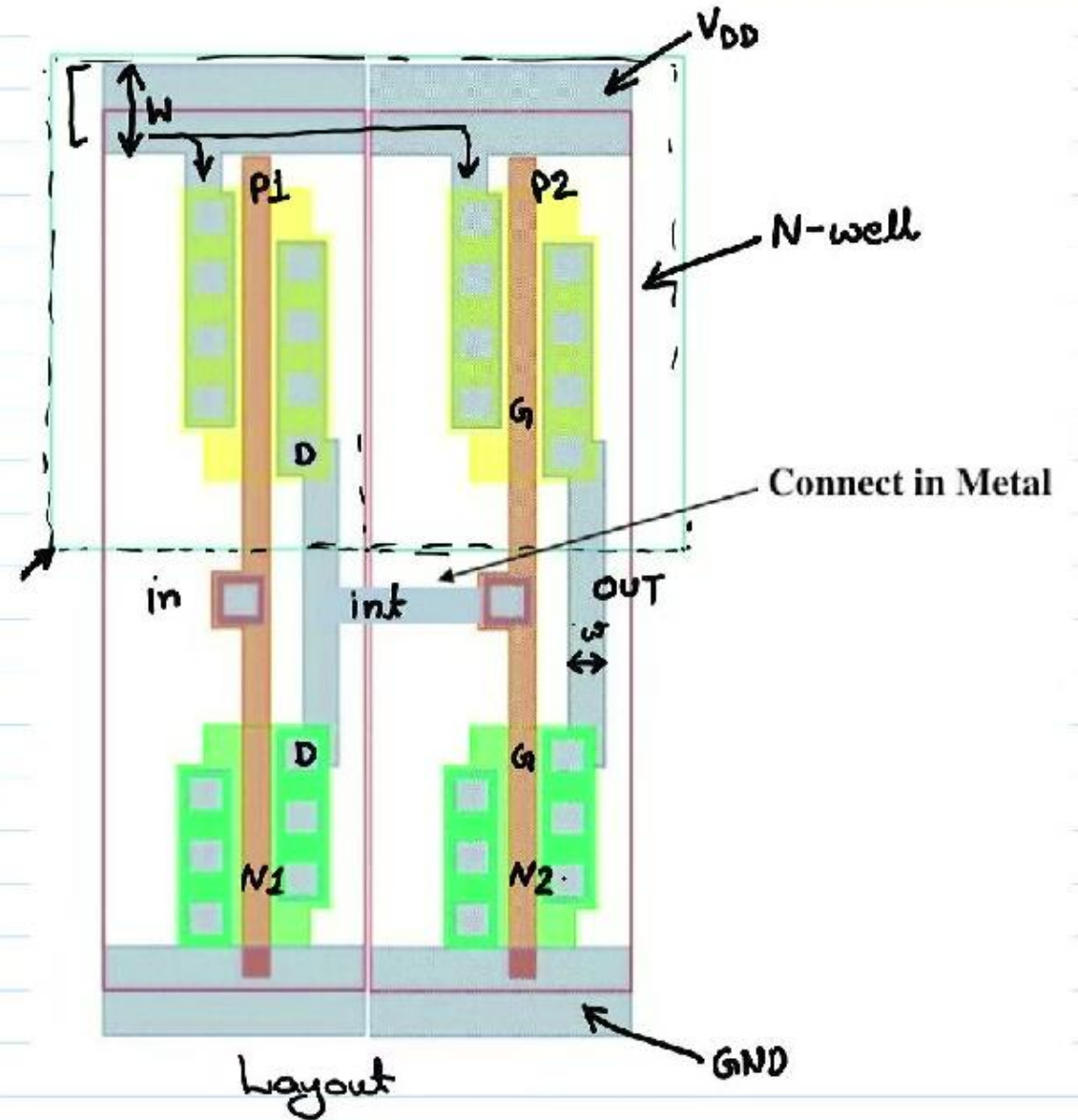
Layout \Rightarrow



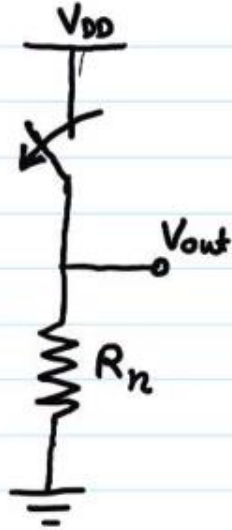
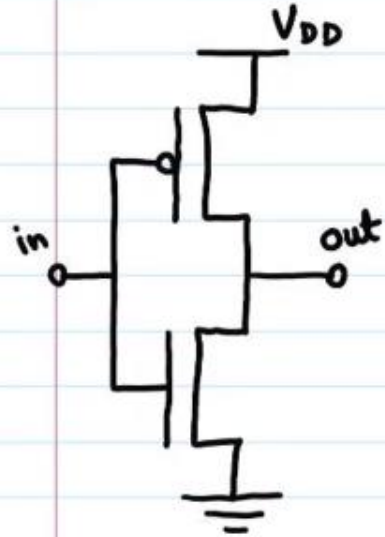
Two Inverters (Schematic vs Layout) :



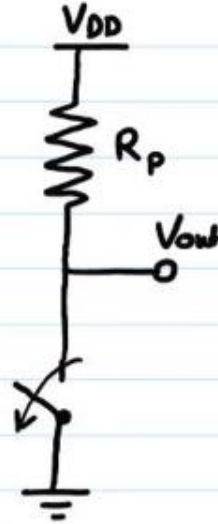
Schematic



CMOS Inverter DC Analysis :



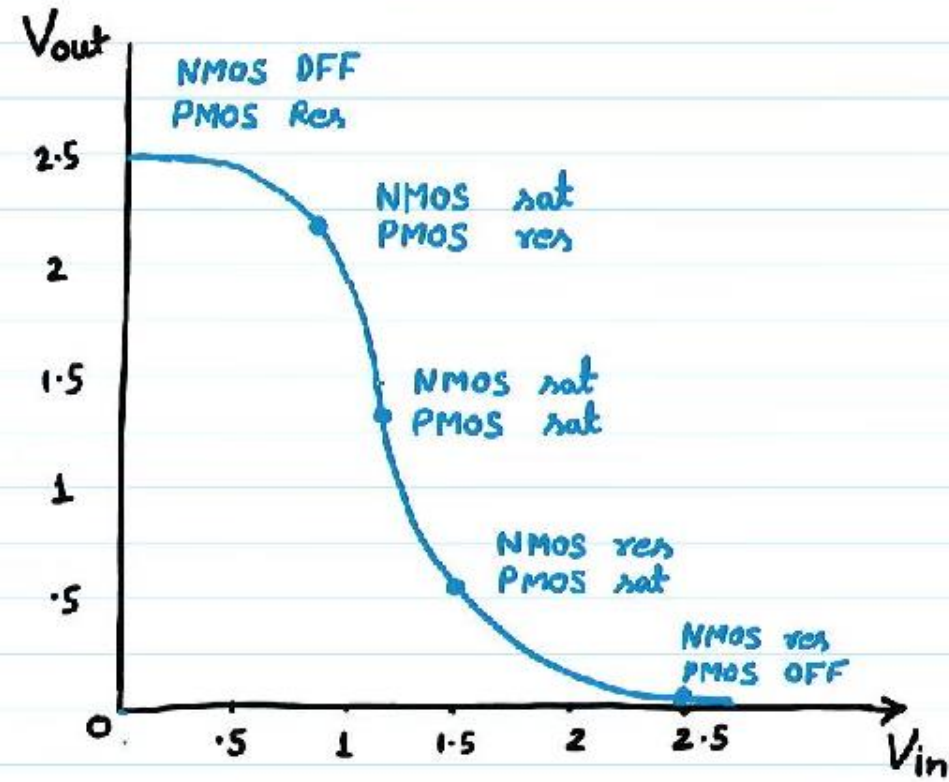
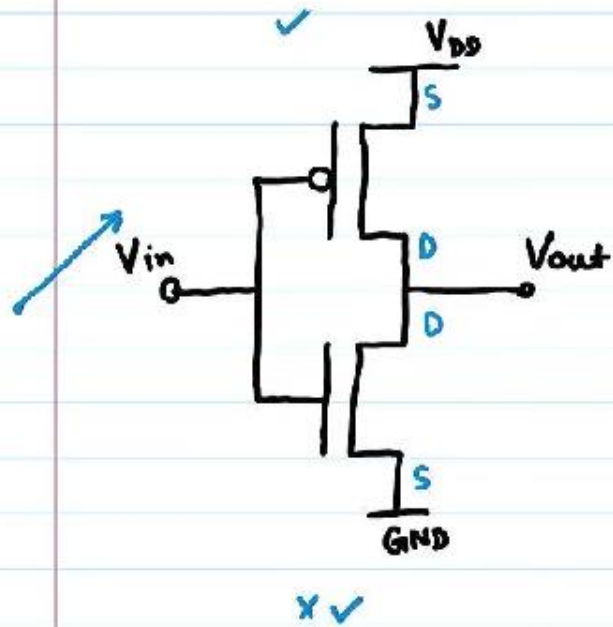
$$V_{in} = V_{DD}$$



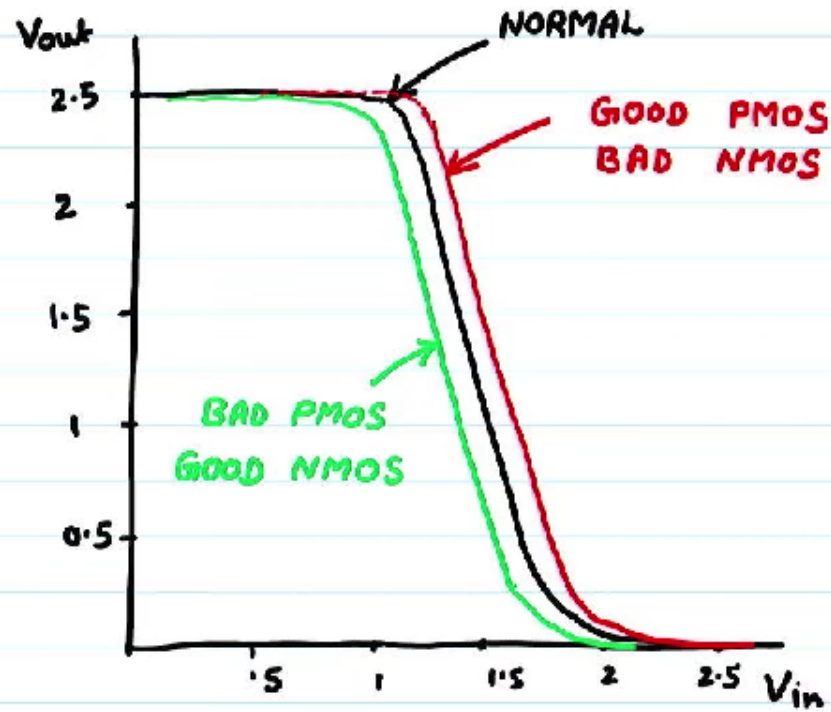
$$V_{in} = 0$$

- Low and High levels equal to V_{DD} and GND.
- Ratioless (logic levels do not depend on device sizes)
- V_{out} is always connected to either V_{DD} or GND.
- I/P impedance is very high
- No static power dissipation.

Voltage - Transfer Characteristics :



Impact of Process Variation :



The good device generally has

- Smaller T_{ox}
- Smaller L_g
- Higher W
- Smaller V_{TH}